

General Description

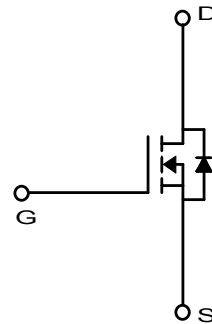
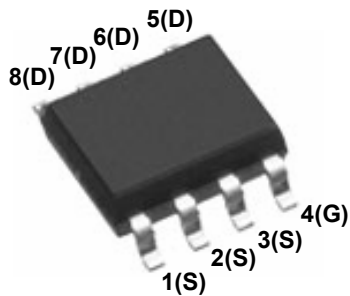
The MDS1652 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. Excellent low $R_{DS(ON)}$, low gate charge and operation for Battery Application.

Features

- $V_{DS} = 30V$
- $I_D = 17A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 6.5m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 9.5m\Omega$ @ $V_{GS} = 4.5V$

Applications

- Li-Ion Battery Application
- Portable Application
- Notebook PC Application



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_a = 25^\circ C$	I_D	17	A
	$T_a = 100^\circ C$		11	A
Pulsed Drain Current		I_{DM}	68	A
Power Dissipation ⁽¹⁾	$T_a = 25^\circ C$	P_D	3.1	W
	$T_a = 100^\circ C$		1.2	W
Single Pulse Avalanche Energy ⁽²⁾		E_{AS}	100	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	40	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	24	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDS1652RP	-55~150°C	SOIC-8	Tape & Reel	Pb Free
MDS1652RH	-55~150°C	SOIC-8	Tape & Reel	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.8	3.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 15A	-	5.1	6.5	mΩ
		V _{GS} = 4.5V, I _D = 12A	-	6.7	9.5	
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 15A	-	30	-	S
Dynamic Characteristics						
Total Gate Charge	Q _{g(10V)}	V _{DS} = 24V, I _D = 15A, V _{GS} = 10V	-	50.0	-	nC
Gate-Source Charge	Q _{gs}		-	4.2	-	
Gate-Drain Charge	Q _{gd}		-	15.0	-	
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	-	2220	-	pF
Reverse Transfer Capacitance	C _{rss}		-	400	-	
Output Capacitance	C _{oss}		-	581	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 15V, I _D = 6.5A, R _G = 4.7Ω	-	12.5	-	ns
Rise Time	t _r		-	22.0	-	
Turn-Off Delay Time	t _{d(off)}		-	77.5	-	
Fall Time	t _f		-	72.0	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 15A, V _{GS} = 0V	-	0.78	1.0	V

Note :

1. Surface mounted RF4 board with 2oz. Copper.
2. Starting $T_J = 25^\circ C$, $L = 1mH$, $I_{AS} = 14A$, $V_{DD} = 15V$, $V_{GS} = 10V$.

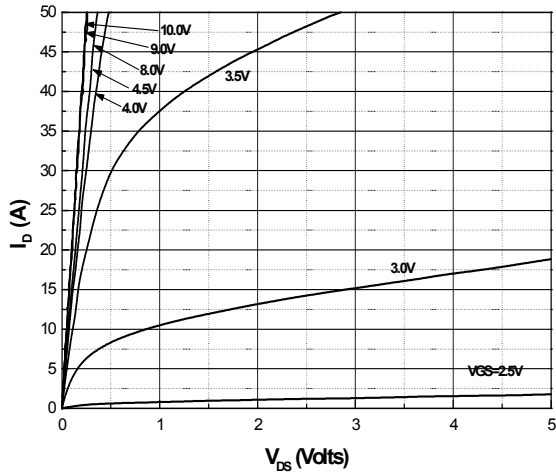


Fig.1 On-Region Characteristics

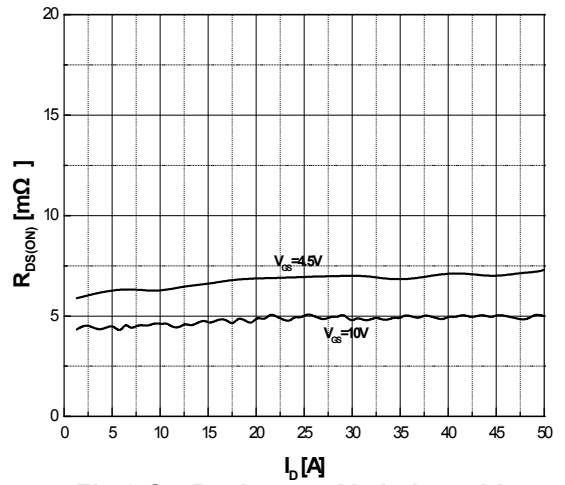


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

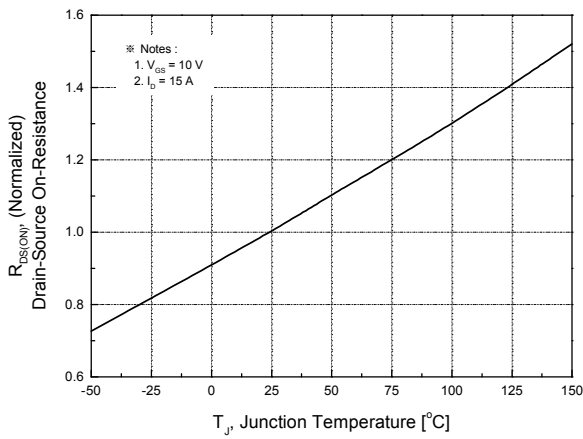


Fig.3 On-Resistance Variation with Temperature

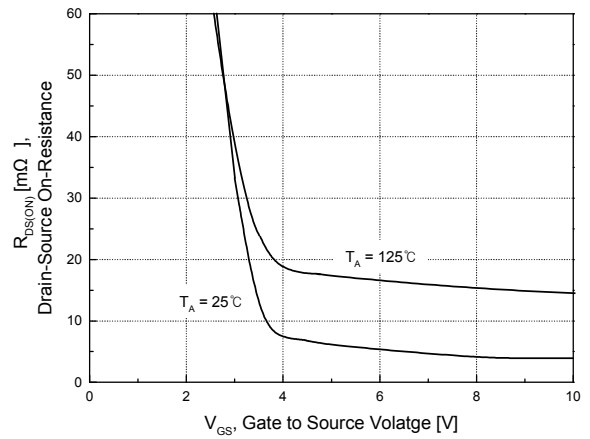


Fig.4 On-Resistance Variation with Gate to Source Voltage

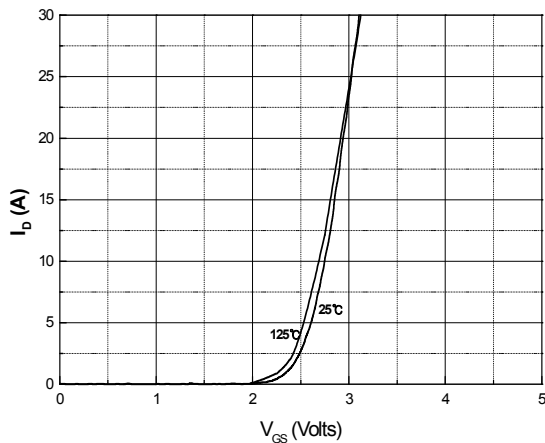


Fig.5 Transfer Characteristics

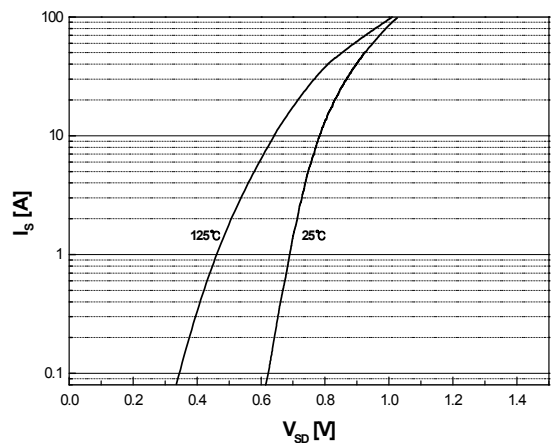
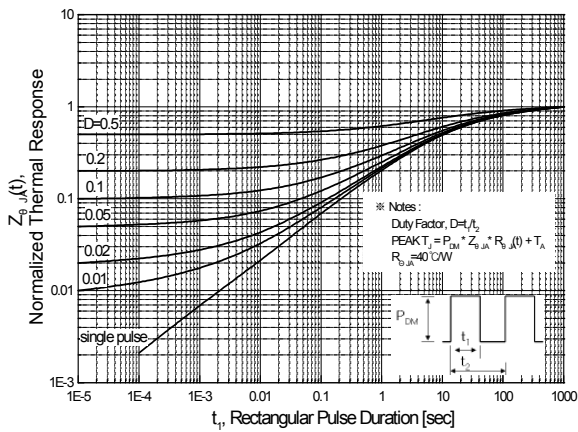
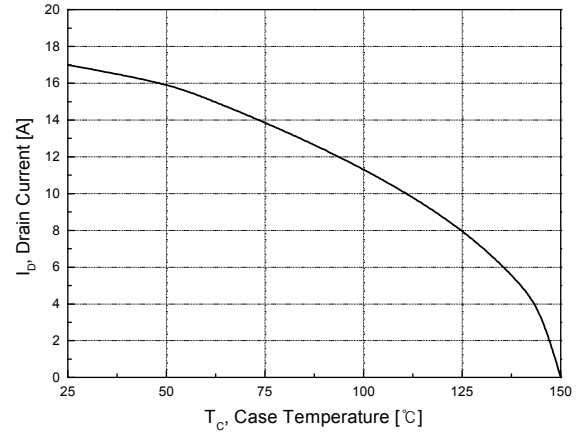
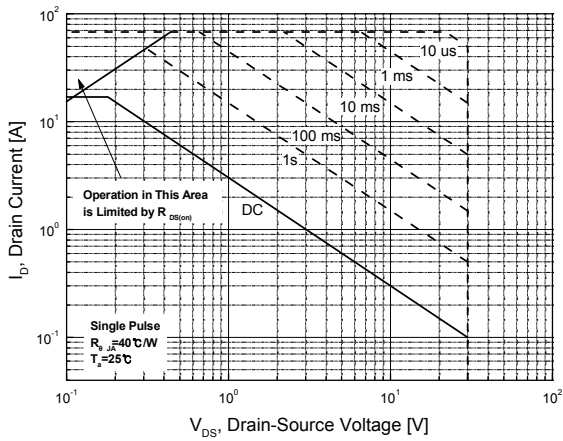
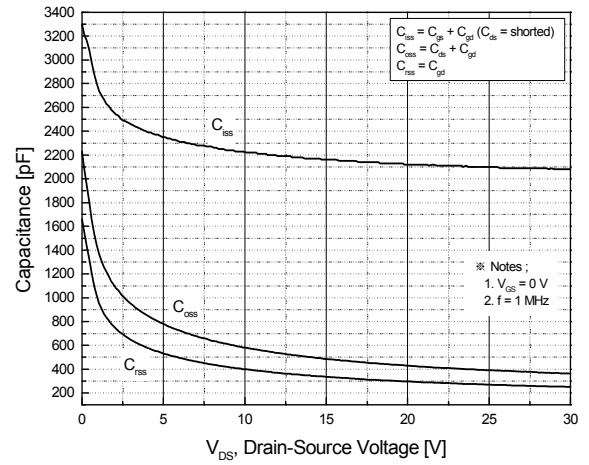
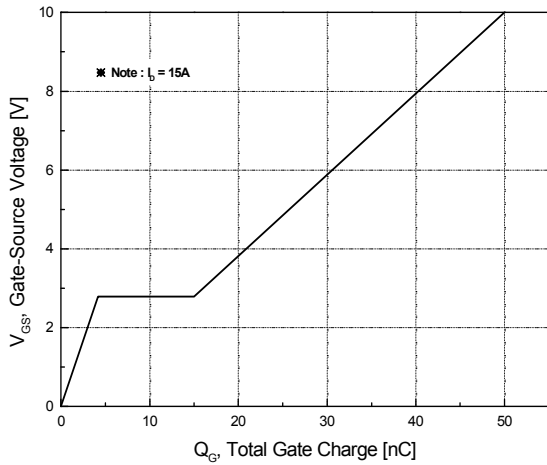


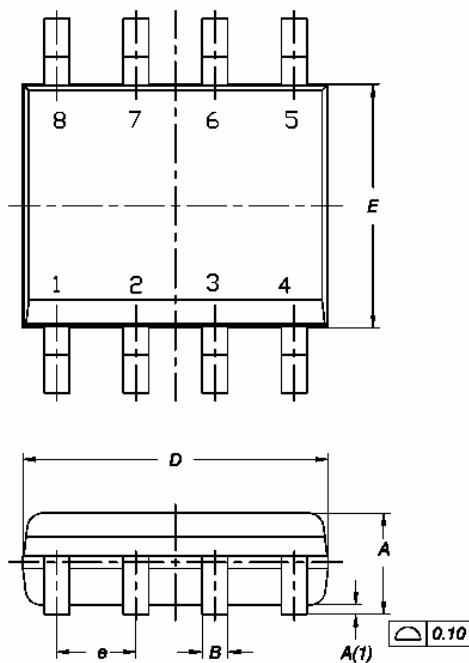
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



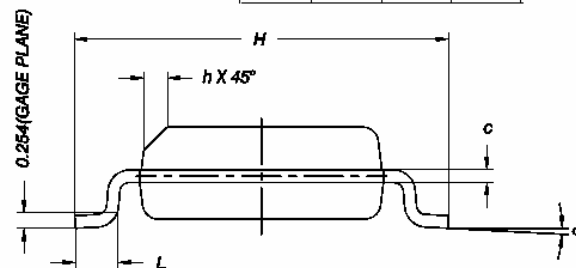
Physical Dimensions

8 Leads, SOIC

Dimensions are in millimeters unless otherwise specified



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.35	1.55	1.75
A(1)	0.10	0.175	0.25
B	0.38	0.445	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27 BSC		
H	5.80	6.00	6.20
L	0.50	0.715	0.93
α	0°	4°	8°
h	0.25	0.375	0.50



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